TOSHIBA 2SJ200

# TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE

# 2 S J 2 0 0

# HIGH POWER AMPLIFIER APPLICATION

• High Breakdown Voltage :  $V_{DSS} = -180 \, V$ 

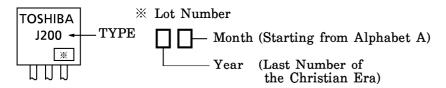
• High Forward Transfer Admittance :  $|Y_{fs}| = 4.0 \text{ S}$  (Typ.)

Complementary to 2SK1529

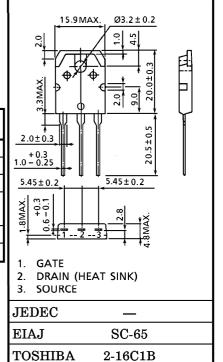
## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$v_{ m DSS}$	-180	V
Gate-Source Voltage	$v_{GSS}$	±20	V
Drain Current	$I_{\mathrm{D}}$	-10	Α
Drain Power Dissipation (Tc = 25°C)	$P_{\mathbf{D}}$	120	w
Channel Temperature	$\mathrm{T_{ch}}$	150	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C

#### **MARKING**



## Unit in mm



Weight: 4.7 g

# ELECTRICAL CHARACTERISTICS (Ta = 25°C)

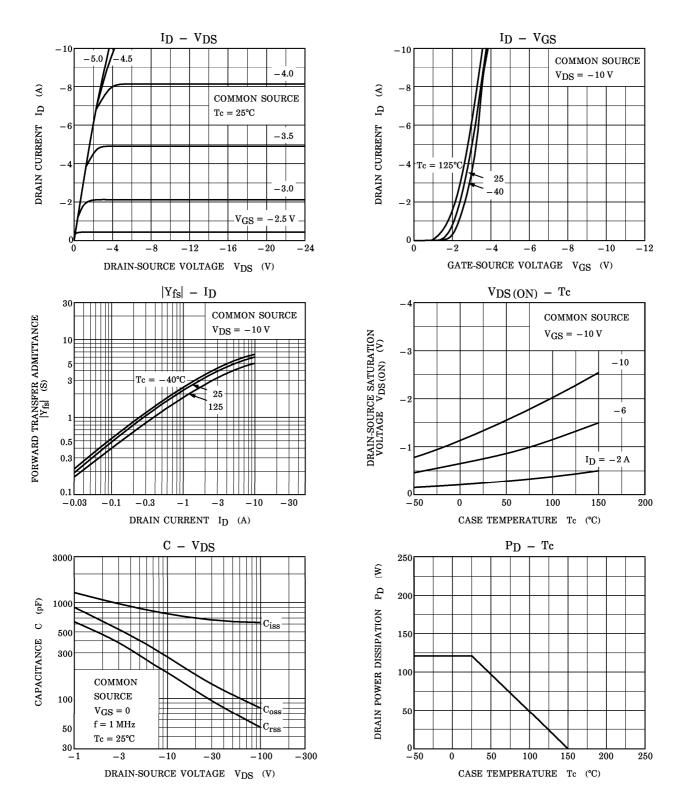
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Drain Cut-Off Current	$I_{ m DSS}$	$V_{DS} = -180 \text{ V}, V_{GS} = 0$	_	_	-1.0	mA
Gate Leakage Current	$I_{GSS}$	$V_{DS} = 0, V_{GS} = \pm 20 V$	_	_	±0.5	$\mu$ A
Drain-Source Breakdown Voltage	V <sub>(BR)</sub> DSS	$I_{D} = -10 \text{ mA}, V_{GS} = 0$	-180	_	_	V
Gate-Source Cut-Off Voltage	VGS (OFF) (Note)	$V_{DS} = -10 \text{ V}, I_{D} = -0.1 \text{ A}$	-0.8	_	-2.8	V
Drain-Source Saturation Voltage	V <sub>DS</sub> (ON)	$I_{\rm D} = -6  {\rm A},  {\rm V_{GS}} = -10  {\rm V}$	_	-1.5	-5.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_{D} = -3 \text{ A}$	_	4.0	_	S
Input Capacitance	$\mathrm{c}_{\mathrm{iss}}$	$V_{DS} = -30 \text{ V}, V_{GS} = 0,$ f = 1 MHz	ı	1300	_	pF
Output Capacitance	$C_{oss}$	$V_{DS} = -30 \text{ V}, V_{GS} = 0,$ f = 1 MHz	_	350	_	pF
Reverse Transfer Capacitance	$\mathrm{c}_{\mathrm{rss}}$	$V_{DS} = -30 \text{ V}, V_{GS} = 0,$ f = 1 MHz		200	_	pF

(Note):  $V_{GS (OFF)}$  Classification  $O: -0.8 \sim -1.6$ ,  $Y: -1.4 \sim -2.8$ This transistor is an electrostatic sensitive device. Please handle with caution.

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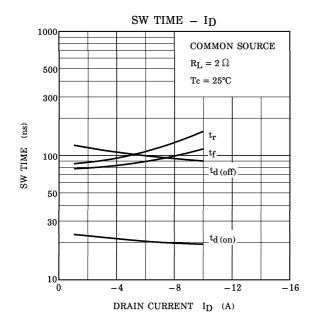
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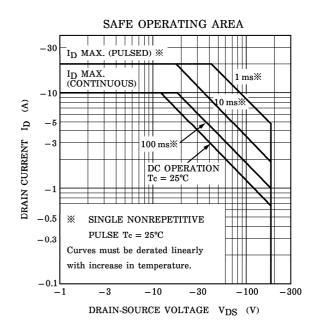
**TOSHIBA** 2SJ200



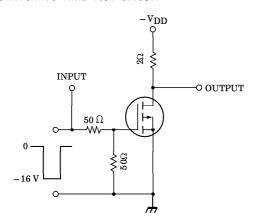
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# SWITCHING TIME TEST CIRCUIT



# **WAVEFORMS**

